

Symbol	Characteristic	Max		Units	
		J309 / J310	*MMBFJ309		
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	350 2.8	225 1.8	mW mW/∘C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W	

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

J309 / J310 / MMBFJ309 / MMBFJ310

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Symbol

 $V_{DS}$ 

 $V_{GS}$ 

 $I_{GF}$ 

T<sub>J</sub>,T<sub>stg</sub>

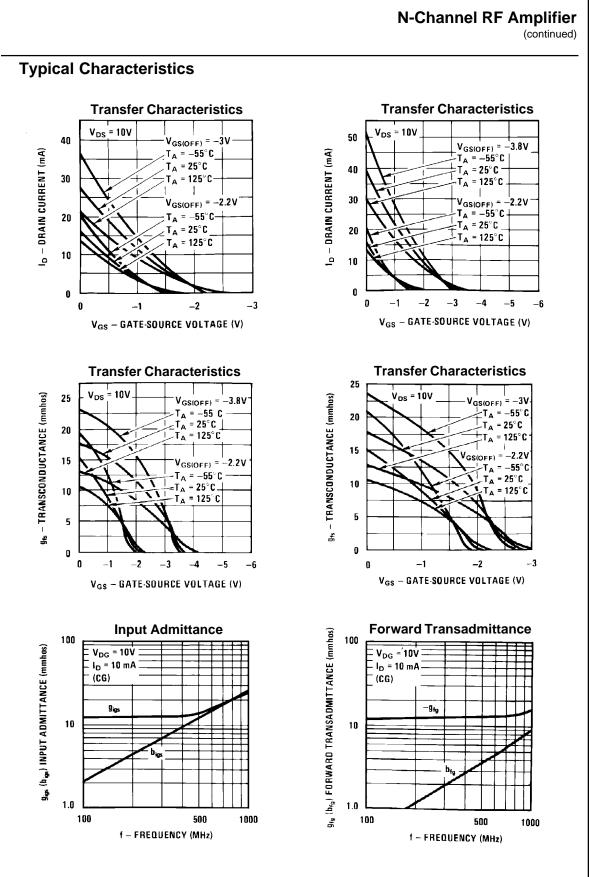
NOTES:

# N-Channel RF Amplifier (continued)

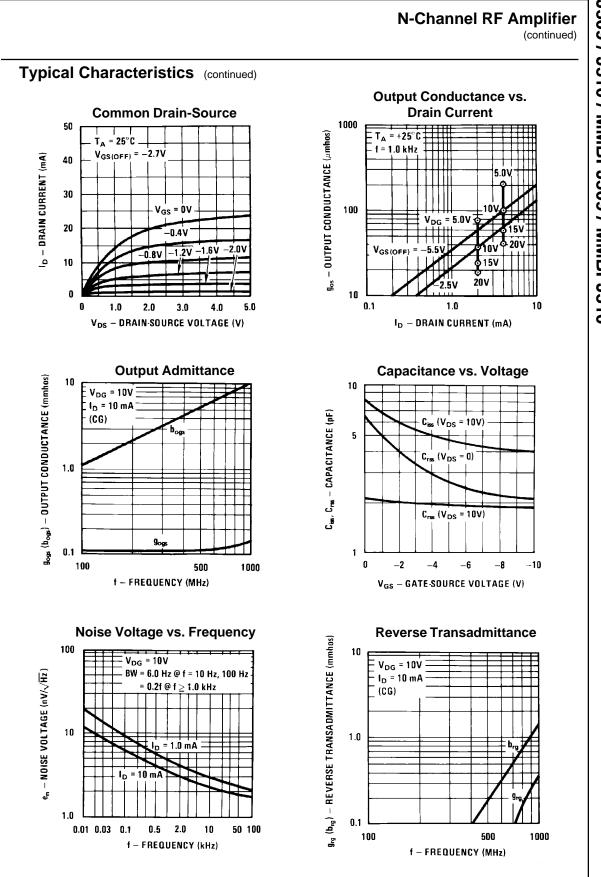
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ontinued)	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
			-			
OFF CHA	RACTERISTICS					
V <sub>(BR)GSS</sub>	Gate-Source Breakdown Voltage	$I_G = -1.0 \ \mu A, \ V_{DS} = 0$	- 25			V
I <sub>GSS</sub>	Gate Reverse Current	V <sub>GS</sub> = - 15 V, V <sub>DS</sub> = 0 V <sub>GS</sub> = - 15 V, V <sub>DS</sub> = 0, T <sub>A</sub> = 125°C			- 1.0 - 1.0	nA μA
$V_{\text{GS(off)}}$	Gate-Source Cutoff Voltage	$\label{eq:VGS} \begin{array}{l} V_{GS} = -\ 15\ V,\ V_{DS} = 0,\ T_A = 125^\circ C \\ \hline V_{DS} = 10\ V,\ I_D = 1.0\ nA \qquad \mbox{J309} \\ \hline \mbox{J310} \end{array}$	- 1.0 - 2.0		- 4.0 - 6.5	V V
ON CHAP	RACTERISTICS Zero-Gate Voltage Drain Current*	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 J309 J310	12 24		30 60	mA mA
V <sub>GS(f)</sub>	Gate-Source Forward Voltage	$V_{DS} = 0, I_G = 1.0 \text{ mA}$			1.0	V
				0 5		no no la c
		J310		0.5		mmhos
Re <sub>(yos)</sub>	Common-Source Output	<b>J310</b> V <sub>DS</sub> = 10, I <sub>D</sub> = 10 mA, f = 100 MHz		0.5 0.25		
ζ- <i>γ</i>	Common-Source Output Conductance Common-Gate Power Gain					
G <sub>pg</sub>	Conductance Common-Gate Power Gain Common-Source Forward	$V_{DS} = 10, I_{D} = 10 \text{ mA}, f = 100 \text{ MHz}$		0.25		mmhos dB
G <sub>pg</sub> Re <sub>(</sub> y <sub>fs)</sub>	Conductance Common-Gate Power Gain	$V_{DS} = 10$ , $I_D = 10$ mA, f = 100 MHz $V_{DS} = 10$ , $I_D = 10$ mA, f = 100 MHz		0.25 16		mmhos dB mmhos
G <sub>pg</sub> Re <sub>(</sub> y <sub>fs)</sub> Re <sub>(</sub> y <sub>ig)</sub>	Conductance Common-Gate Power Gain Common-Source Forward Transconductance	$V_{DS} = 10$ , $I_D = 10$ mA, f = 100 MHz $V_{DS} = 10$ , $I_D = 10$ mA, f = 100 MHz $V_{DS} = 10$ , $I_D = 10$ mA, f = 100 MHz	10,000	0.25 16 12	20,000	mmhos dB mmhos mmhos μmhos
G <sub>pg</sub> Re(Vfs) Re(Vig) gfs	Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward	$\begin{split} V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ J309 \end{split}$		0.25 16 12		mmhos dB mmhos mmhos μmhos
G <sub>pg</sub> Re(Vfs) Re(Vig) gfs gos	Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output	$\begin{split} V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ J309 \\ J310 \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz} \end{split}$		0.25 16 12	18,000	mmhos dB mmhos mmhos μmhos μmhos μmhos
G <sub>pg</sub> Re(Vfs) Re(Vig) gfs gos gfg	Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output Conductance	$\begin{split} V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 100 \ \text{MHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 1.0 \ \text{MHz} \\ \textbf{J309} \\ \textbf{J310} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz} \\ \textbf{J309} \\ \textbf{J310} \\ V_{DS} &= 10, \ I_D = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz} \\ \textbf{J309} \\ \textbf{J310} \end{split}$		0.25 16 12 12 13,000	18,000	mmhos dB mmhos mmhos μmhos μmhos μmhos μmhos μmhos
G <sub>pg</sub> Re(yfs) Re(yfg) gfs gos gfg gog	Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output Conductance Common-Gate Forward Conductance	$\begin{split} & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & \mathbf{J309} \\ & \mathbf{J310} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & \mathbf{J309} \\ & \mathbf{J310} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & \mathbf{J309} \\ & \mathbf{J310} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & \mathbf{J309} \\ & \mathbf{J310} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & \mathbf{J309} \\ & \mathbf{J310} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & \mathbf{J309} \\ & \mathbf{J310} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & \mathbf{J309} \\ & \mathbf{J300} \\ & \mathbf{J309} \\ & \mathbf{J309} \\ & \mathbf{J309} \\ & \mathbf{J300} \\ & \mathbf{J30}$		0.25 16 12 12 13,000 12,000 100	18,000	mmhos dB mmhos μmhos μmhos μmhos μmhos μmhos μmhos
Gpg     Re(Yfs)     Re(yig)     gfs     gos     gfg     Gog     Cdg	Conductance   Common-Gate Power Gain   Common-Source Forward   Transconductance   Common-Gate Input Conductance   Common-Source Forward   Transconductance   Common-Source Output   Conductance   Common-Gate Forward Conductance   Common-Gate Forward Conductance   Common-Gate Forward Conductance	$\begin{split} & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & J309 \\ & J310 \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & J309 \\ & J310 \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & J309 \\ & J310 \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & J309 \\ & J310 \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & J309 \\ & J310 \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & J309 \\ & J310 \\$		0.25 16 12 12 13,000 12,000 100 150	18,000	mmhos dB mmhos μmhos μmhos μmhos μmhos μmhos μmhos
Re(yos)     Gpg     Re(yfs)     Re(yig)     gfs     gos     gfg     Gog     Cdg     Csg     NF	Conductance   Common-Gate Power Gain   Common-Source Forward   Transconductance   Common-Gate Input Conductance   Common-Source Forward   Transconductance   Common-Source Output   Conductance   Common-Source Output   Conductance   Common-Gate Forward Conductance   Common-Gate Output Conductance   Drain-Gate Capacitance	$\begin{split} & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 100 \text{ MHz} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & \mathbf{J309} \\ & \mathbf{J310} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & \mathbf{J309} \\ & \mathbf{J310} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & \mathbf{J309} \\ & \mathbf{J310} \\ & V_{DS} = 10,  I_D = 10 \text{ mA},  f = 1.0 \text{ kHz} \\ & \mathbf{J309} \\ & \mathbf{J310} \\ & V_{DS} = 0,  V_{GS} = -10,  f = 1.0 \text{ MHz} \end{split}$		0.25 16 12 12 13,000 12,000 100 150 2.0	18,000 150 2.5	mmhos dB mmhos mmhos μmhos μmhos μmhos μmhos μmhos pF

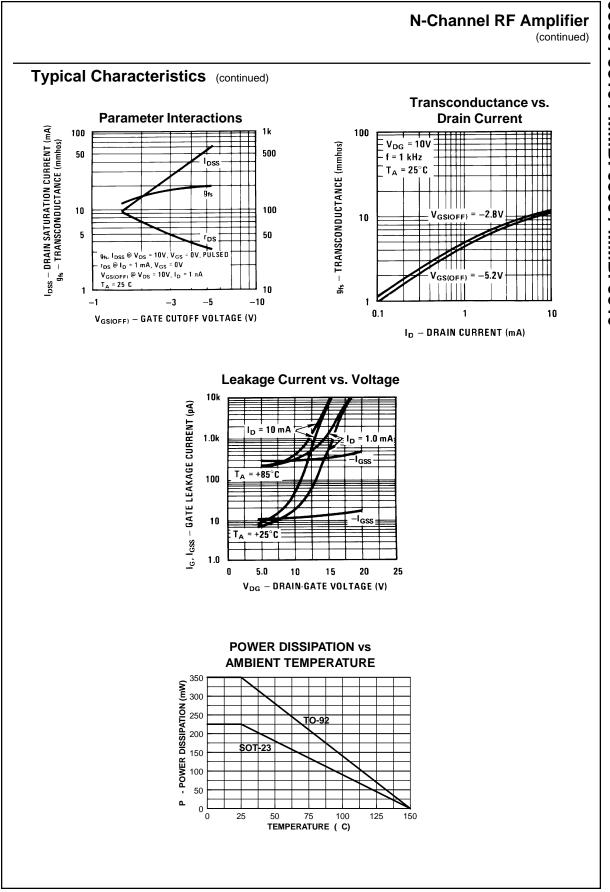
\*Pulse Test: Pulse Width  $\pm$  300 ms, Duty Cycle  $\pm$  2.0%



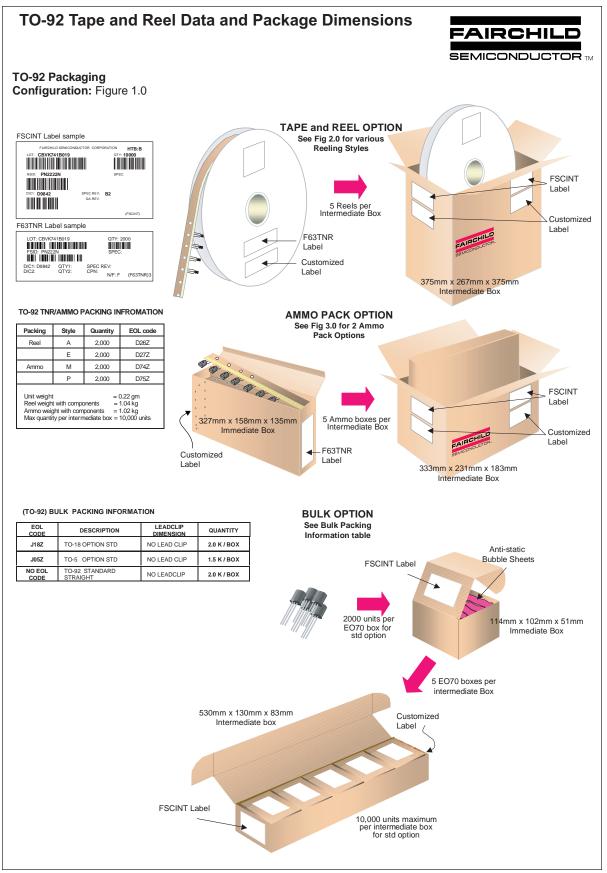
**J309 / J310 / MMBFJ309 / MMBFJ310** 



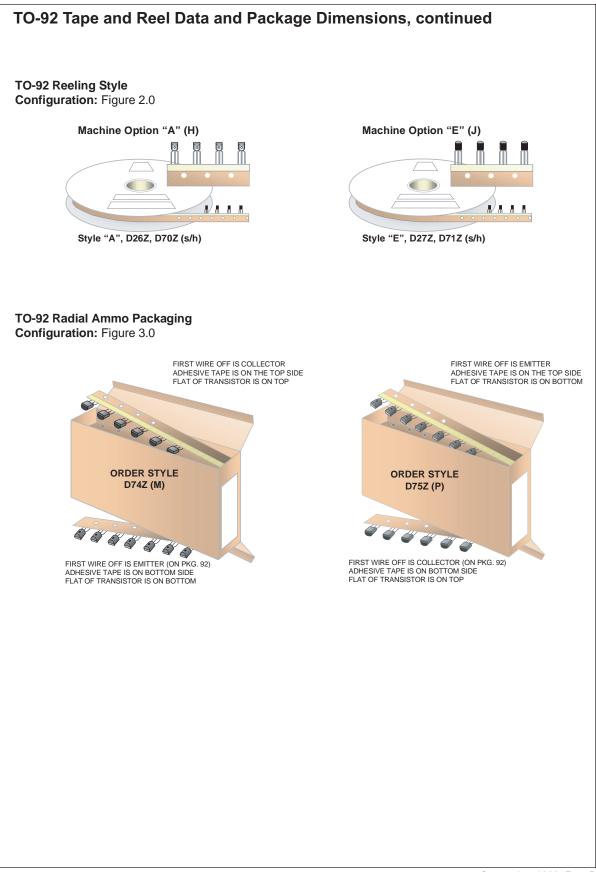
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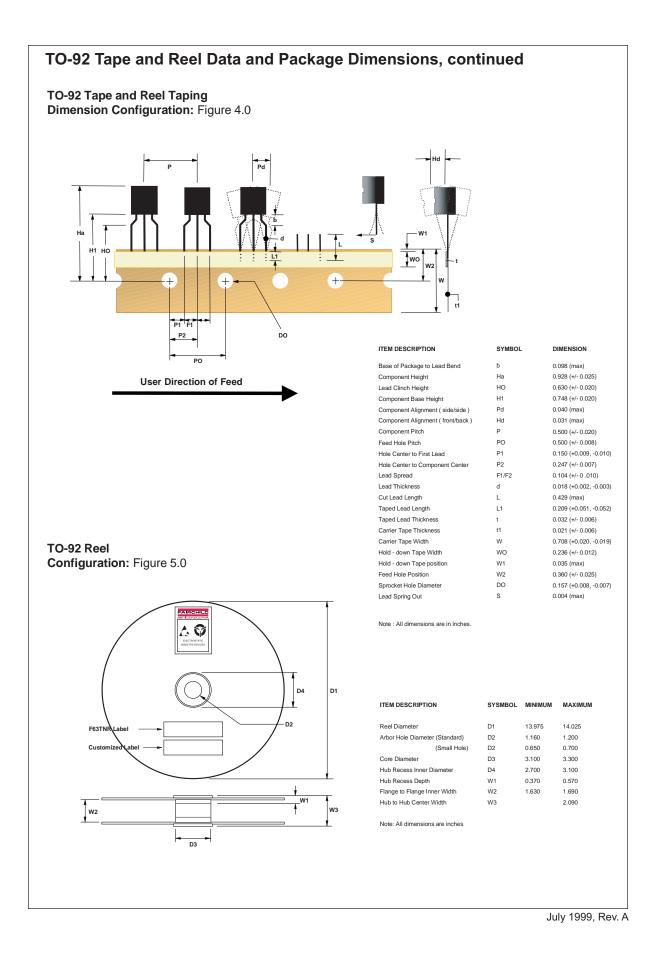


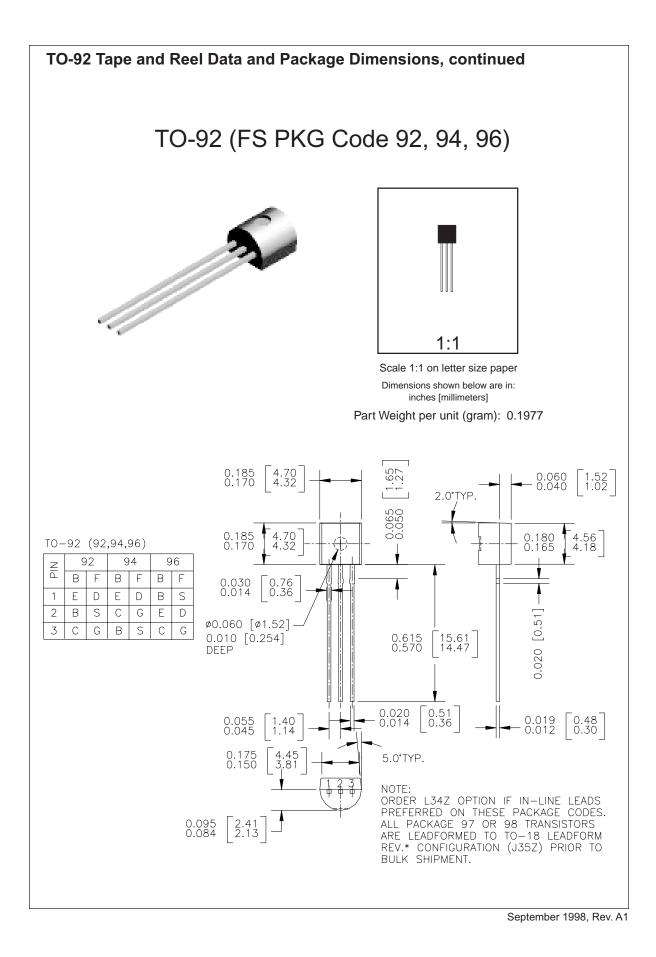
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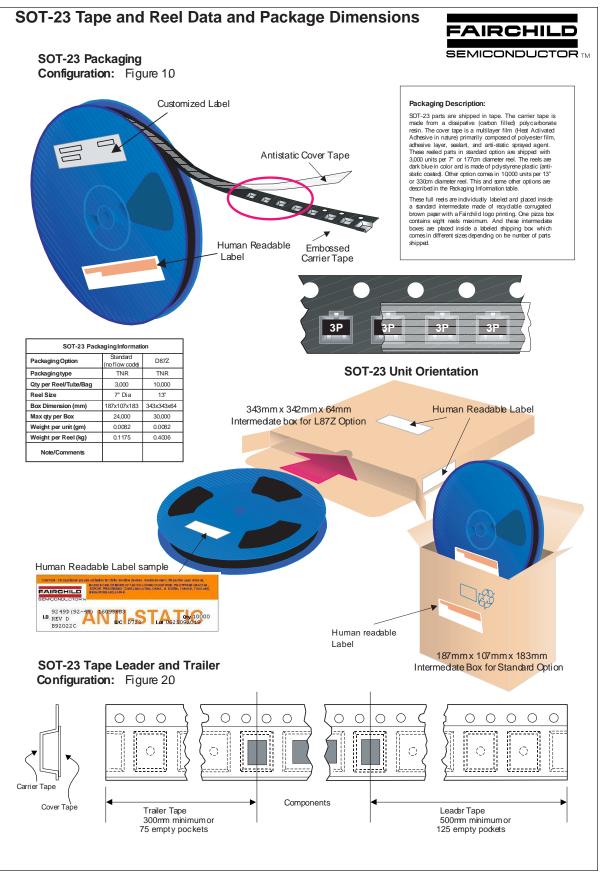


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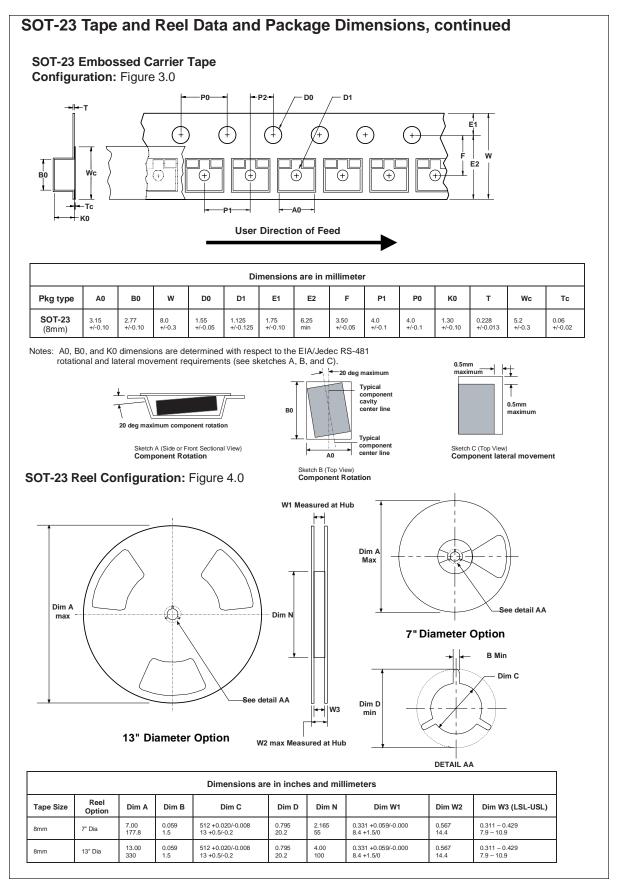




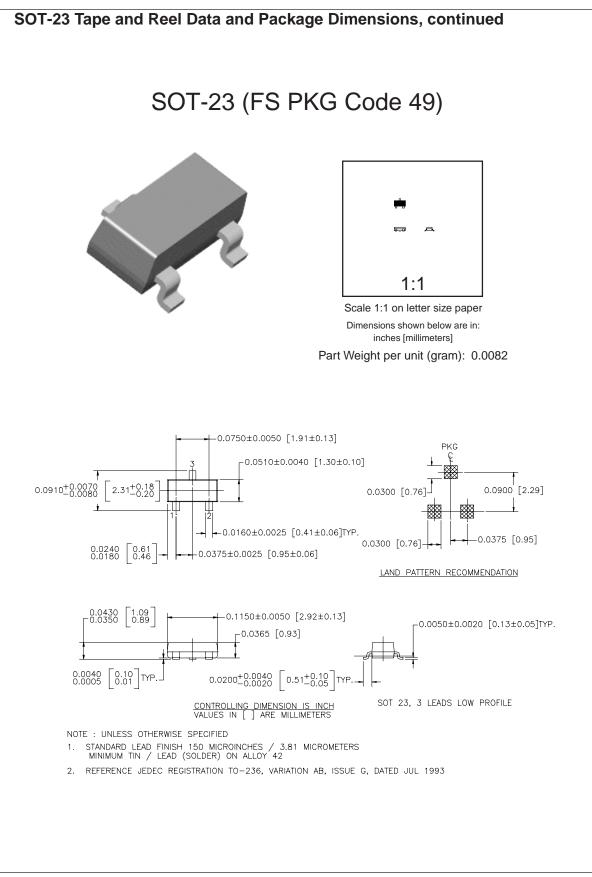




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September 1998, Rev. A1

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